imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half-wave silicon gate-controlled, solid-state devices are needed.

Features

- Glass Passivated Junctions with Center Gate Geometry for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 V
- These are Pb–Free Devices

MAXIMUM RATINGS* ($T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
$\begin{array}{l} \mbox{Peak Repetitive Off-State Voltage (Note 1)} \\ (T_J = -40 \ to \ 125^\circ C, \ Sine \ Wave \ 50 \ to \ 60 \\ \ Hz; \ Gate \ Open) \\ & 2N6400 \\ & 2N6401 \\ & 2N6402 \\ & 2N6403 \\ & 2N6404 \\ & 2N6405 \end{array}$	V _{DRM,} V _{RRM}	50 100 200 400 600 800	V
On-State Current RMS (180° Conduction Angles; T _C = 100°C)	I _{T(RMS)}	16	A
Average On-State Current (180° Conduction Angles; T_C = 100°C)	I _{T(AV)}	10	A
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, $T_J = 25^{\circ}$ C)	I _{TSM}	160	A
Circuit Fusing Considerations (t = 8.3 ms)	l ² t	145	A ² s
Forward Peak Gate Power (Pulse Width \leq 1.0 $\mu s,T_C$ = 100°C)	P _{GM}	20	W
Forward Average Gate Power (t = 8.3 ms, $T_C = 100^{\circ}C$)	P _{G(AV)}	0.5	W
Forward Peak Gate Current (Pulse Width \leq 1.0 $\mu s,T_C$ = 100°C)	I _{GM}	2.0	A
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

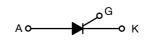
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

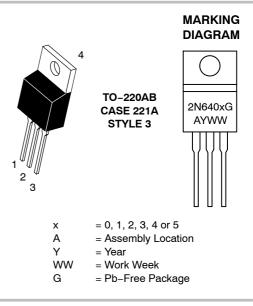
 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



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	PIN ASSIGNMENT
1	Cathode
2	Anode
3	Gate
4	Anode

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

THERMAL CHARACTERISTICS

Characteristic		Symbol	Ма	IX	U	nit
Thermal Resistance, Junction-to-Case		R_{\thetaJC}	1.	5	°C	W/
Maximum Lead Temperature for Soldering Purposes 1/8 in from Case for 10 Seconds		TL	260		°C	
ELECTRICAL CHARACTERISTICS ($T_{C} = 25^{\circ}$	C unless otherwise noted.)					
Characteristic	0	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					-	
*Peak Repetitive Forward or Reverse Blocking Cu $(V_{AK} = Rated V_{DRM} \text{ or } V_{RRM}, Gate Open)$	irrent T _J = 25°C T _J = 125°C	I _{DRM} , I _{RRM}		_	10 2.0	μA mA
ON CHARACTERISTICS						
*Peak Forward On–State Voltage (I_{TM} = 32 A Peak,	Pulse Width \leq 1 ms, Duty Cycle \leq 2%)	V _{TM}	-	-	1.7	V
*Gate Trigger Current (Continuous dc) $(V_D = 12 \text{ Vdc}, R_L = 100 \Omega)$	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	I _{GT}		9.0 -	30 60	mA
*Gate Trigger Voltage (Continuous dc) (V_D = 12 Vdc, R_L = 100 Ω)	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	V _{GT}		0.7	1.5 2.5	V
Gate Non-Trigger Voltage (V_D = 12 Vdc, R_L = 100 S	2), T _C = +125°C	V _{GD}	0.2	-	-	V
*Holding Current (V _D = 12 Vdc, Initiating Current = 200 mA, Gate	$T_{C} = 25^{\circ}C$ Open) * $T_{C} = -40^{\circ}C$	IH	-	18 _	40 60	mA
Turn-On Time (I_{TM} = 16 A, I_{GT} = 40 mAdc, V_D = F	Rated V _{DRM})	t _{gt}	-	1.0	-	μs
Turn-Off Time (I_{TM} = 16 A, I_R = 16 A, V_D = Rated	V _{DRM}) T _C = 25°C T _J = +125°C	tq		15 35		μs
DYNAMIC CHARACTERISTICS						
Critical Rate-of-Rise of Off-State Voltage (V _D = R T _J = +125°C	ated V _{DRM} , Exponential Waveform)	dv/dt	-	50	-	V/µs

*Indicates JEDEC Registered Data.

Voltage Current Characteristic of SCR

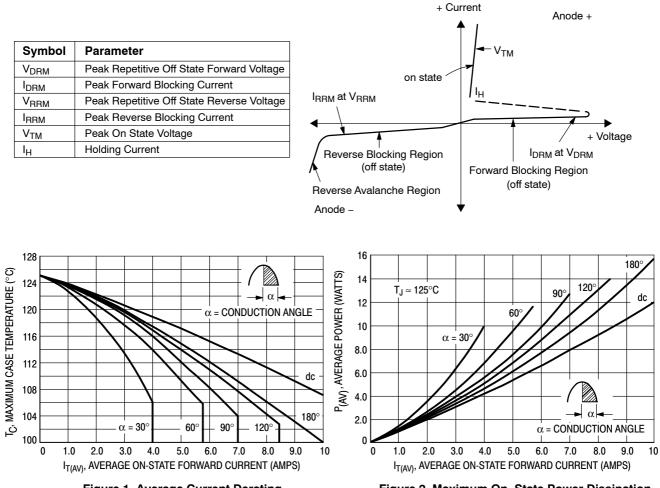
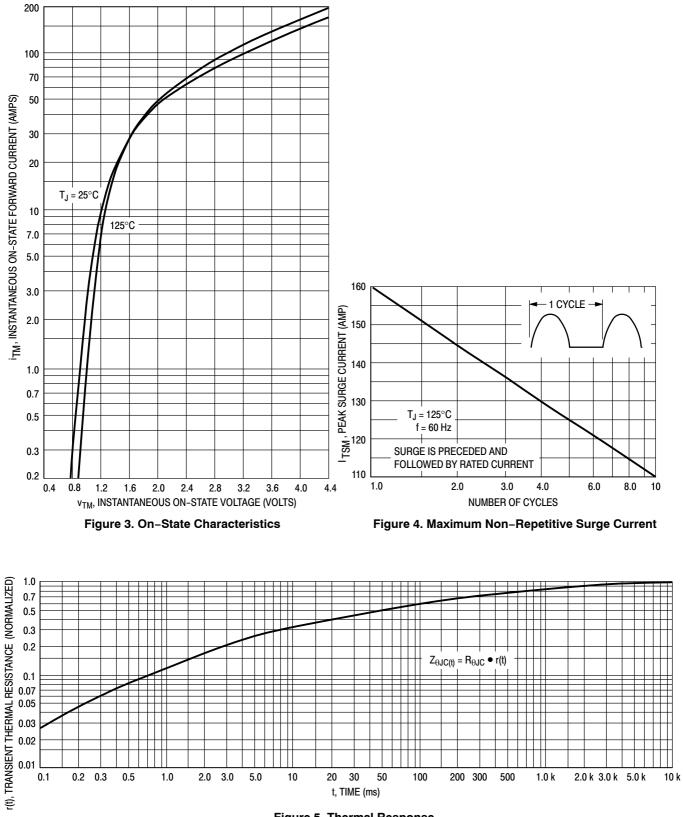


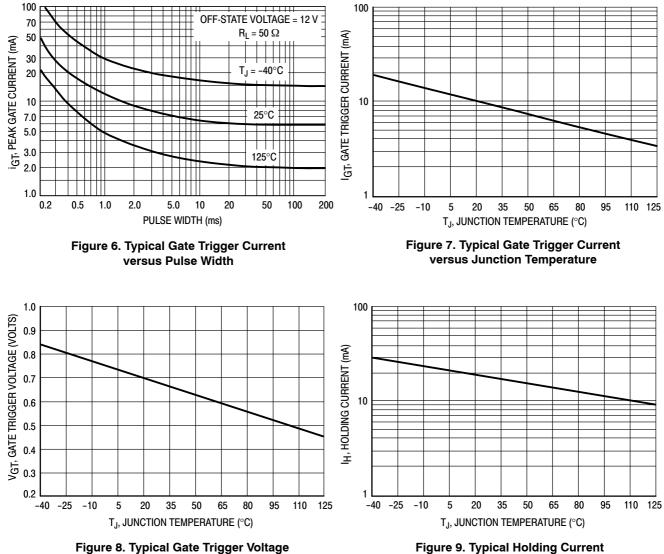
Figure 1. Average Current Derating

Figure 2. Maximum On-State Power Dissipation

3



TYPICAL CHARACTERISTICS



versus Junction Temperature

Figure 9. Typical Holding Curren versus Junction Temperature

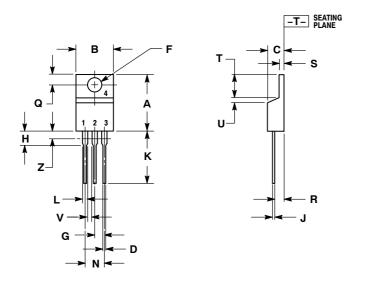
5

ORDERING INFORMATION

Device	Package	Shipping [†]
2N6400G	TO-220AB (Pb-Free)	
2N6401G	TO-220AB (Pb-Free)	500 Haita / Davi
2N6402G	TO-220AB (Pb-Free)	500 Units / Box
2N6403G	TO-220AB (Pb-Free)	
2N6403TG	TO-220AB (Pb-Free)	50 Units / Rail
2N6404G	TO-220AB (Pb-Free)	500 Unite / Dev
2N6405G	TO-220AB (Pb-Free)	500 Units / Box

PACKAGE DIMENSIONS





	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
۷	0.045		1.15	
Z		0.080		2.04

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI

Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

2. 3. ANODE GATE

ANODE 4.

Littelfuse products are not designed for, and shall not be used for, any purpose (including, without limitation, automotive, military, aerospace, medical, life-saving, life-sustaining or nuclear facility applications, devices intended for surgical implant into the body, or any other application in which the failure or lack of desired operation of the product may result in personal injury, death, or property damage) other than those expressly set forth in applicable Littelfuse product documentation. Warranties granted by Littelfuse shall be deemed void for products used for any purpose not expressly set forth in applicable Littelfuse documentation. Littelfuse shall not be liable for any claims or damages arising out of products used in applications not expressly intended by Littelfuse as set forth in applicable Littelfuse documentation. The sale and use of Littelfuse products is subject to Littelfuse Terms and Conditions of Sale, unless otherwise agreed by Littelfuse.

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